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Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the litem (book, magazine, journal, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published PROGRESS IN RF INDUCTORS ON SILICON - UNDERSTANDING SUBSTRATE LOSSES" by Joachim N. Burghartz - IBM Research Division, T. J. Watson Research Center, P. O. Box 218, Yorktown Heights, New York 10598 USA Center, P. O. Box 218, Yorktown Heights, Ne	Olleer 1	_		
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